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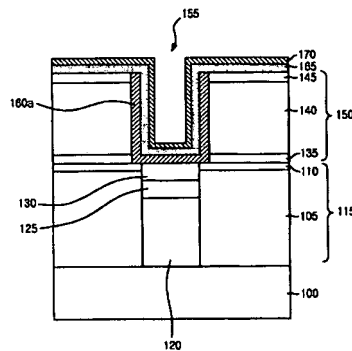
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(54) METHOD FOR MANUFACTURING MEMORY DEVICE

(57) Abstract:

PURPOSE: A fabrication method of a DRAM device having a high aspect ratio is provided to improve a step coverage and a crystalization of a BST(Barium Strontium Titanate) by using double deposition of ALD(Atomic Layer Deposition)-BST and CVD-BST.

CONSTITUTION: A first interlayer dielectric(115) having a contact hole is formed on a semiconductor substrate(100). A contact plug stacked sequentially a polysilicon layer(120), a silicide layer(125) and a barrier metal(130) is filled into the contact hole. After forming a second interlayer dielectric(150) on the resultant structure, a storage node hole(155) is formed to expose the contact plug by selectively etching the second interlayer dielectric(150). A lower electrode pattern(160a) is formed on the entire surface of the storage node hole. A dielectric film is formed on the lower electrode pattern(160a) by sequentially depositing an ALD-BST film(165) and a CVD-BST film(170). Then, an upper electrode is formed on the dielectric film.



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